

**AMENDMENTS TO THE CLAIMS**

*Please enter the following amendments:*

1. (Currently Amended) A two-beam semiconductor laser device comprising:  
a two-beam semiconductor element having first and second semiconductor laser elements that can be driven independently and that are formed integrally on a substrate; and  
a submount having, mounted on a front part thereof, the two-beam semiconductor laser element with a light-emitting face thereof directed forward and having first and second electrode pads connected to electrodes of the first and second semiconductor laser elements by being kept in contact therewith,  
wherein no photodetector is provided ~~behind the two-beam semiconductor laser element~~ on the submount, ~~[[and]]~~  
wherein the first and second electrode pads are formed to extend farther behind the two-beam semiconductor laser element, and are wire-bonded behind the two-beam semiconductor laser element, and  
wherein a lateral width of the submount along the front part of the submount is 400  $\mu\text{m}$  or more but 700  $\mu\text{m}$  or less.

2. (Original) The two-beam semiconductor laser device of claim 1,  
wherein the first and second electrode pads are wire-bonded at a rear end of the submount.

3. (Previously Presented) The two-beam semiconductor laser device of claim 1,  
wherein a distance from the rear end of the two-beam semiconductor laser element to a  
position where the first and second electrode pads are wire-bonded is 300  $\mu\text{m}$  or shorter.

4. (Canceled)

5. (Currently Amended) The two-beam semiconductor laser device of claim 1,  
further comprising a metal frame;  
wherein the submount is mounted ~~in a package composed of a~~ directly on the frame, and  
~~a resin member~~  
no photodetector is directly mounted on the frame.

6. (Currently Amended) The two-beam semiconductor laser device of claim 5,  
wherein the two-beam semiconductor laser device is built as a three-terminal two-beam  
semiconductor laser device having only three terminals.

7. (New) The two-beam semiconductor laser device of claim 5,  
further comprising three bonding wires, each bonded to a location behind the submount  
and to one of an electrode of the two-beam semiconductor element, the first electrode pad, and  
the second electrode pad.